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Dr. Lin has been pioneering deep-UV lithography since 1975, multilayer resist systems since 1979, simulation of 2D partially coherent imaging since 1980, exposure-defocus methodology since 1980, scaling equations of resolution and depth of focus since 1986, k_1 reduction since 1987, proofs of 1X mask limitations since 1987, vibration in optical imaging since 1989, electrical measurement of contact holes since 1989, E-G tree for x-ray proximity printing since 1990, experimental demonstration of the impact of mask reflectivity on imaging since 1990, optimum lens NA since 1990, attenuated phase-shifting mask since 1991, signamization since 1996, LWD-η and LWD-β since 1999, nonparaxial scaling equations of resolution and depth of focus since 2000, 193-nm immersion lithography since 2002, and

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